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MOSFET – P-Channel, POWERTRENCH

-20 V, -4 A, 100 mΩ

FDC642P-F085, FDC642P-F085P

Features

- Typ $R_{DS(on)}$ = 52.5 mΩ at $V_{GS} = -4.5$ V, $I_D = -4$ A
- Typ $R_{DS(on)}$ = 75.3 mΩ at $V_{GS} = -2.5$ V, $I_D = -3.2$ A
- Fast Switching Speed
- Low Gate Charge (6.9 nC Typical)
- High Performance Trench Technology for Extremely Low $R_{DS(on)}$
- SUPERSOT™ –6 Package: Small Footprint (72% Smaller than Standard SO–8); Low Profile (1 mm Thick)
- AEC-Q101 Qualified and PPAP Capable
- This Device is Pb-Free and is RoHS Compliant

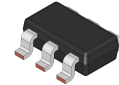
Applications

- Load Switch
- Battery Protection
- Power management



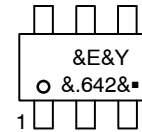
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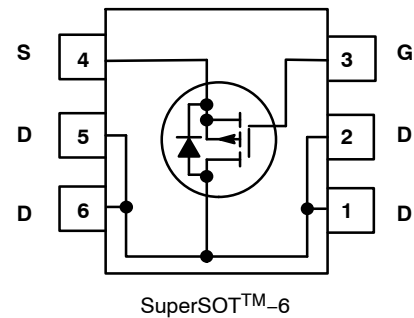
TSOT23 6-Lead
CASE 419BL

MARKING DIAGRAM



XXX = Specific Device Code
 &E = Space Designator
 &Y = Year of Production
 &. = Pin One Identifier
 ▪ = Pb-Free Package

PINOUT



ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FDC642P-F085, FDC642P-F085P

MOSFET MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	-20	V
V_{GS}	Gate to Source Voltage	± 8	V
I_D	Drain Current - Continuous ($V_{GS} = 4.5\text{ V}$) - Pulsed	-4 -20	A
E_{AS}	Single Pulse Avalanche Energy (Note 1)	72	mJ
P_D	Power Dissipation	1.2	W
T_J, T_{STG}	Operating and Storage Temperature	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Starting $T_J = 25^\circ\text{C}$, $L = 14.1\text{ mH}$, $I_{AS} = -3.2\text{ A}$

THERMAL CHARACTERISTICS

Symbol	Parameter	Ratings	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	30	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, 1 in^2 Copper pad Area	103	

PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDC642P	FDC642P-F085	SSOT-6	7"	8 mm	3000 Units
FDC642P	FDC642P-F085P	SSOT-6	7"	8 mm	3000 Units

FDC642P–F085, FDC642P–F085P

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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OFF CHARACTERISTICS

B _V DSS	Drain to Source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0 V	-20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -16 V, V _{GS} = 0 V	-	-	-1	μA
		V _{DS} = -16 V, V _{GS} = 0 V, T _A = 150°C	-	-	-250	
I _{GSS}	Gate to Source Leakage Current	V _{GS} = ±8 V	-	-	±100	nA

ON CHARACTERISTICS

V _{GS(th)}	Gate to Source Threshold Voltage	V _{GS} = V _{DS} , I _D = -250 μA	-0.4	-0.7	-1.5	V
r _{DS(on)}	Drain to Source On Resistance	V _{GS} = -4.5 V, I _D = -4 A	-	52.5	65	mΩ
		V _{GS} = -2.5 V, I _D = -3.2 A	-	75.3	100	
		V _{GS} = 4.5 V, I _D = -4 A, T _J = 125 °C	-	72.7	105	
g _{FS}	Forward Transconductance	V _{DD} = -5 V, I _D = -4 A	-	10	-	S

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	V _{GS} = 0 V, V _{DS} = -10 V	-	630	-	pF
C _{oss}	Output Capacitance	f = 1 MHz	-	160	-	pF
C _{rss}	Reverse Transfer Capacitance		-	65	-	pF
R _g	Gate Resistance	f = 1 MHz	-	4.4	-	Ω
Q _{g(TOT)}	Total Gate Charge at -4.5 V	V _{GS} = 0 V to -4.5 V, V _{DD} = -10 V, I _D = -4 A	-	6.9	9.0	nC
Q _{gs}	Gate to Source Gate Charge	V _{DD} = -10 V	-	1.2	-	nC
Q _{gd}	Gate to Drain "Miller" Charge	I _D = -4 A	-	1.8	-	nC

SWITCHING CHARACTERISTICS

t _{on}	Turn-On Time	V _{DD} = -10 V, I _D = -1 A, V _{GS} = -4.5 V, R _{GS} = 6 Ω	-	-	23	ns
t _{d(on)}	Turn-On Delay Time		-	7.3	-	ns
t _r	Rise Time		-	5.5	-	ns
t _{d(off)}	Turn-Off Delay Time		-	23.2	-	ns
t _f	Fall Time		-	9.6	-	ns
t _{off}	Turn-Off Time		-	-	53	ns

DRAIN-SOURCE DIODE CHARACTERISTICS

V _{SD}	Source to Drain Diode Voltage	I _{SD} = -1.3 A	-	-	-1.25	V
		I _{SD} = -0.65 A	-	-	-1.0	
t _{rr}	Reverse Recovery Time	I _{SD} = -1.3 A, dI _{SD} /dt = 100 A/μs	-	17	22	ns
Q _{rr}	Reverse Recovery Charge		-	5.6	7.3	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

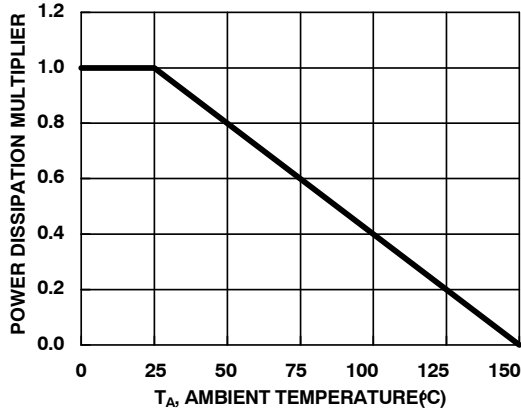


Figure 1. Normalized Power Dissipation vs. Ambient Temperature

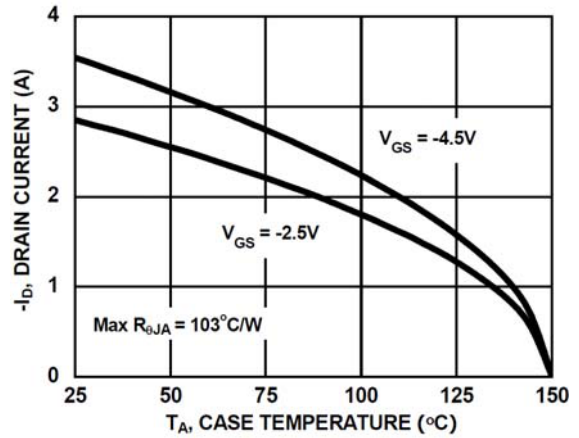


Figure 2. Maximum Continuous Drain Current vs. Ambient Temperature

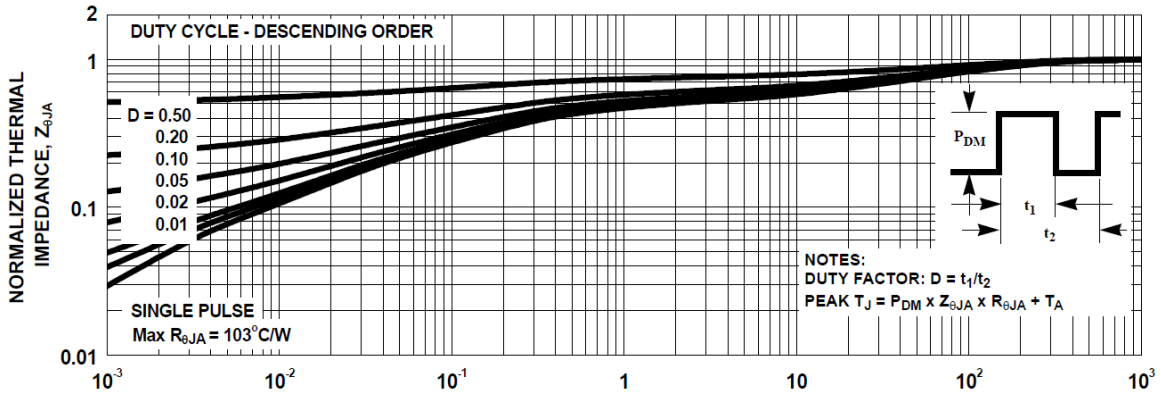


Figure 3. Normalized Maximum Transient Thermal Impedance

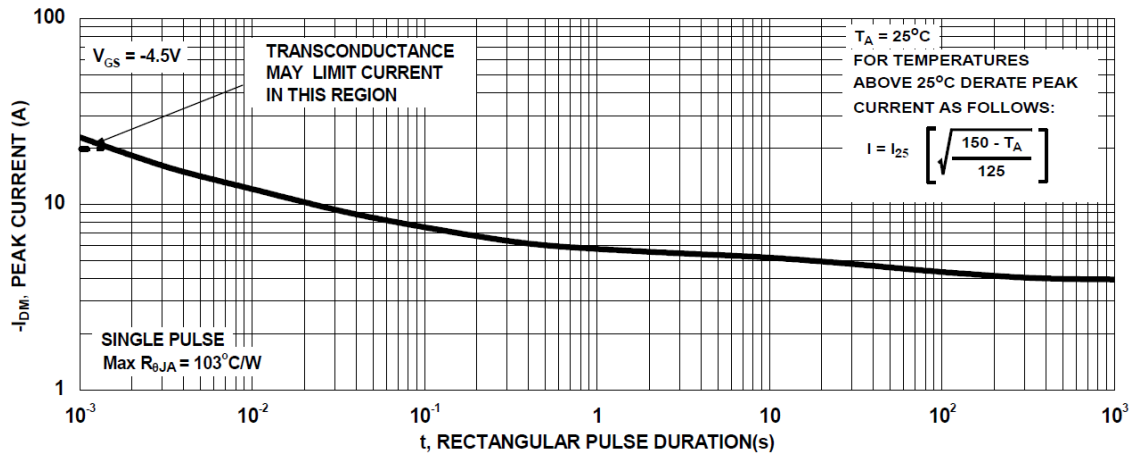


Figure 4. Peak Current Capability

TYPICAL CHARACTERISTICS (continued)

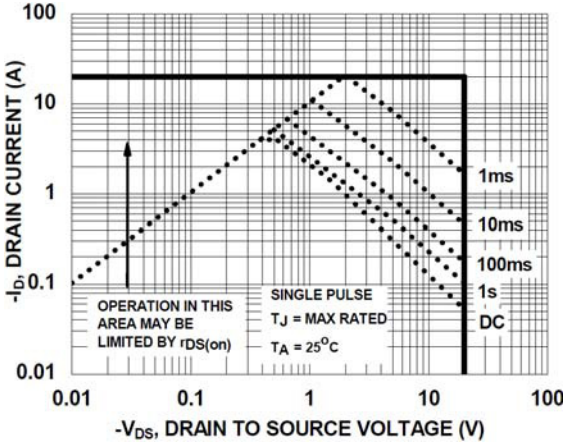


Figure 5. Forward Bias Safe Operating Area

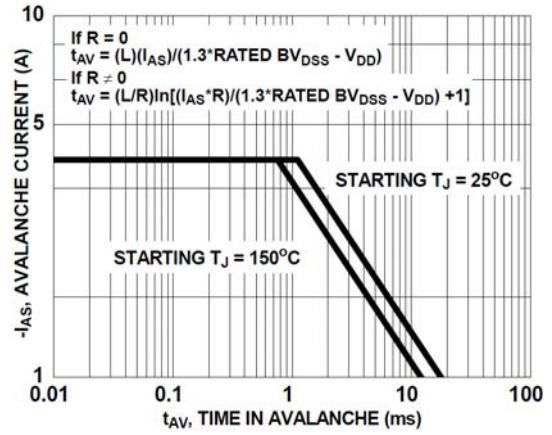


Figure 6. Unclamped Inductive Switching Capability

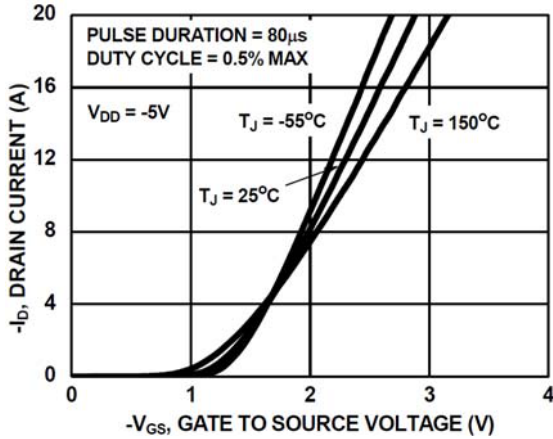


Figure 7. Transfer Characteristics

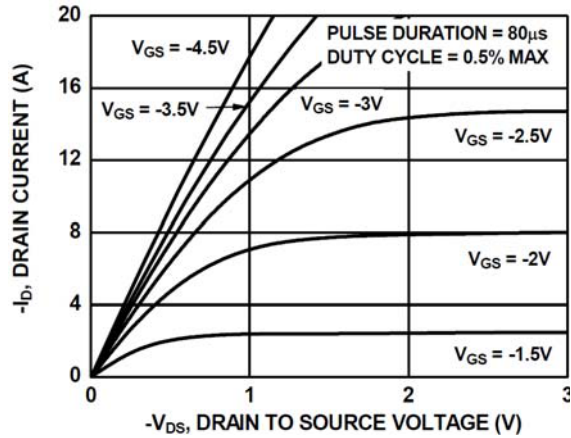


Figure 8. Saturation Characteristics

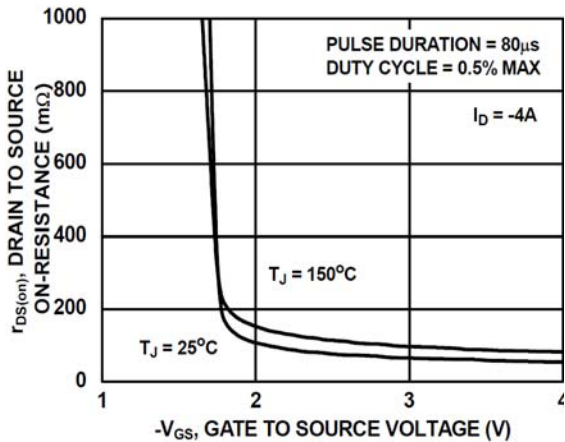


Figure 9. Drain to Source On-Resistance Variation vs. Gate to Source Voltage

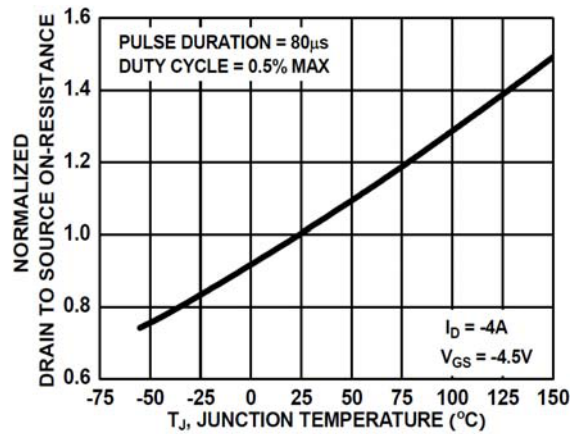


Figure 10. Normalized Drain to Source On-Resistance vs. Junction Temperature

FDC642P-F085, FDC642P-F085P

TYPICAL CHARACTERISTICS $T_J = 25^\circ\text{C}$ unless otherwise noted (continued)

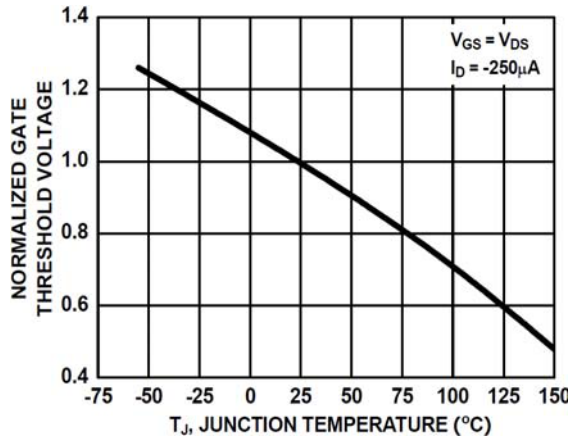


Figure 11. Normalized Gate Threshold Voltage vs. Junction Temperature

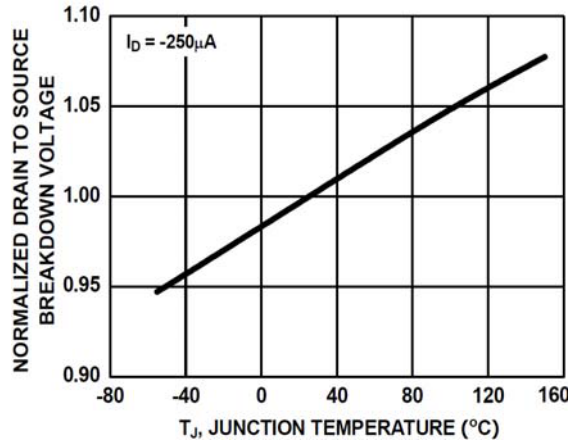


Figure 12. Normalized Drain to Source Breakdown Voltage vs. Junction Temperature

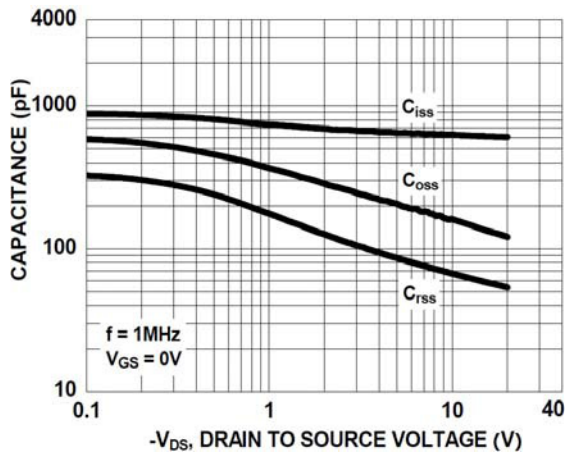


Figure 13. Capacitance vs. Drain to Source Voltage

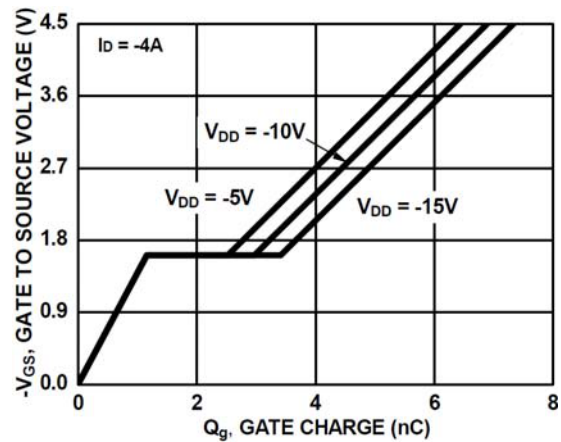


Figure 14. Gate Charge vs. Gate to Source Voltage

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

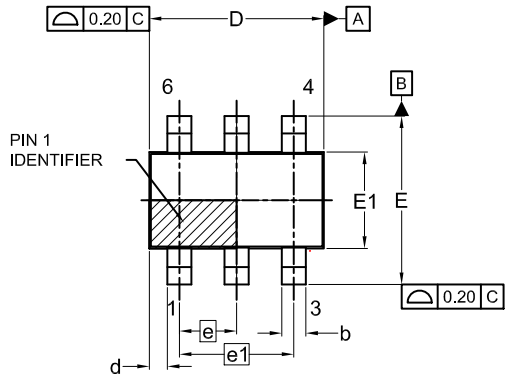
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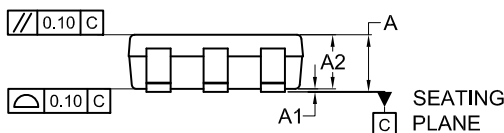
SCALE 2:1

TSOT23 6-Lead CASE 419BL ISSUE A

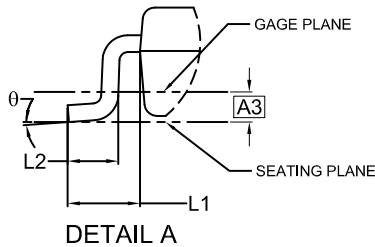
DATE 31 AUG 2020



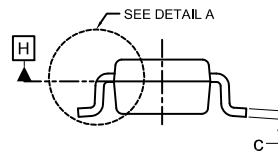
TOP VIEW



FRONT VIEW

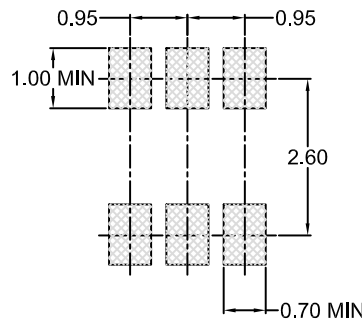


DETAIL A



SIDE VIEW

SYMM
⌀



LAND PATTERN
RECOMMENDATION

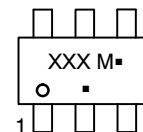
*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.25MM PER END. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.
4. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	0.05	0.10
A2	0.70	0.85	1.00
A3	0.25 BSC		
b	0.25	0.38	0.50
c	0.10	0.18	0.26
D	2.80	2.95	3.10
d	0.30 REF		
E	2.50	2.75	3.00
E1	1.30	1.50	1.70
e	0.95 BSC		
e1	1.90 BSC		
L1	0.60 REF		
L2	0.20	0.40	0.60
⌀	0°	--	10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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